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Substitute for Form 1449A/PTO

# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Complete If Known

Application Number 10/620,516

Filing Date July 16, 2003

First Named Inventor Udayakumar et al.

Group Art Unit

Examiner Name

Attorney Docket No. TI-35996

Sheet 1

1

of

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## U.S. PATENT DOCUMENTS

Exam. Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
SWL	AA	6,144,060		Park et al.	11/07/2000	Entire Document
SWL	AB	6,225,656	B1	Cuchiaro et al.	05/01/2001	Entire Document
	AC					
	AD					
	AF					
	AG					
	AH					

## FOREIGN PATENT DOCUMENTS

Exam. Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>3</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>2</sup> (if known)				
	BA							
	BB							
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## OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Exam. Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
SWL	CA	Notes taken at the International Symposium on Applications of Ferroelectrics Conference in Nara, Japan in May, 2002. The speaker was H. Nagel of Infineon Technologies and Toshiba Corporation, Key Technologies for High Density FeRAM Application, one page.	
	CB		
	CC		
	CD		
	CE		
	CF		
	CG		
	CH		

Examiner Signature	CRANE	Date Considered	3/12/04
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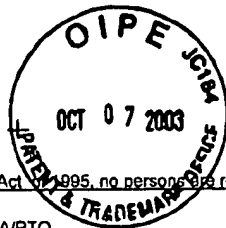
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US and Foreign Patent Documents: <sup>1</sup>Unique citation designation number. <sup>2</sup>See attached Kinds of U.S. Patent Documents. <sup>3</sup>Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to place a check mark here if English language Translation is attached.

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				Application Number	10/620,516
				Filing Date	July 16, 2003
				First Named Inventor	Udayakumar t al.
				Group Art Unit	
				Examiner Name	
Sheet	2	of	2	Attorney Docket No.	TI-35996

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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SWC	CG	"Comparison Between HCP CVD and PECVD Silicon Nitride for Advanced Interconnect Applications", J. YOTA, M. JANANI, L.E. CAMILLETTI, A. KAR-ROY, Q.Z. LIU, C. NGUYEN, M.D. WOO J. HANDER, and P. VAN CLEEMPUT, IEEE, 2000, pgs. 76-78.	
SWC	CH	"Hydrogen Role on the Properties of Amorphous Silicon Nitride", F. DE BRITO MOTS, J.F. JUSTO and A. FAZZIO, Journal of Applied Physics, Volume 86, Number 4, August 15, 1999, pgs. 1843-1847.	
	CI		
	CJ		
	CK		
	CL		
	CM		
	CN		
	CO		
	CP		

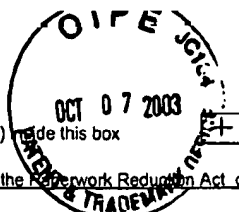
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		Number	Kind Code <sup>2</sup> (if known)			
SWC	AA	5,452,178		Emesh et al.	09/19/1995	Entire Document
	AB	5,972,722		Visokay et al.	10/26/1999	Entire Document
	AC	6,090,697		Xing et al.	07/18/2000	Entire Document
	AD	6,177,351	B1	Beratan et al.	01/23/2001	Entire Document
	AE	6,242,299	B1	Hickert	06/05/2001	Entire Document
	AF	6,261,967	B1	Athavale et al.	07/17/2001	Entire Document
	AG	6,291,251	B1	Nam	09/18/2001	Entire Document
	AH	6,423,592	B1	Sun	07/23/2002	Entire Document
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	AM	6,611,014	B1	Kanaya et al.	08/26/2003	Entire Document
	AN	2001/0034106	A1	Moise et al.	10/25/2001	Entire Document
	AO	2001/0044205	A1	Gilbert et al.	11/22/2001	Entire Document

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SWC	CA	"FeRAM Tutorial", ALI SHEIKHOESLAMI and P. GLENN GULAK, A survey of circuit Innovations in Ferroelectric random-access memories, Proceedings of the IEEE, Vol. 88, No. 3, May, 2000, 3 pages, taken from the Internet at: <a href="http://www.eecg.toronto.edu/~ali/ferro/tutorial.html">http://www.eecg.toronto.edu/~ali/ferro/tutorial.html</a> .		
	CB	"A survey of Circuit Innovations in Ferroelectric Random Access Memories", ALI SHEIKHOESLAMI and P. GLENN GULAK, Proceedings of the IEEE, Vol. 88, No. 5, May, 2000, pp. 667-689.		
	CC	"Generic CVD Reactor", CVD Basics, DANIEL M. DOBKIN, Dec. 7, 2001, 3 pages, taken from the Internet at: <a href="http://www.batn.t.com/nigmatics/semiconductor_processing/CVD_Fundamentals/introdu...">http://www.batn.t.com/nigmatics/semiconductor_processing/CVD_Fundamentals/introdu...</a>		
	CD	"Physical Vapor Deposition", Cougar Labs, Inc., Dec. 7, 2001, 9 pages, taken from the Internet at: <a href="http://www.cougarlabs.com/pvd1.html">http://www.cougarlabs.com/pvd1.html</a> .		
	CE	"The Hydrogen Content of Plasma-Deposited silicon Nitride", W. A. LANFORD and M. J. RAND, American Institute of Physics, J. Appl. Phys. 49(4), April, 1978, Pgs. 2473-2477.		
SWC	CF	"Free Energy Model for the Analysis of Bonding in a-Si <sub>x</sub> N <sub>y</sub> H <sub>z</sub> Alloys", Z. YIN and W. SMITH, J. Vac. Sci. Technol. A Volume 9, No. 3, May/June, 1991, pg. 972.		

CRANE

3/18/04